

Dual N-Channel 2.5-V (G-S) Input Protected Load Switch

PRODUCT SUMMARY

V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)	Q_g (Typ.)
20	0.030 at $V_{GS} = 4.5$ V	4.5	7.6
	0.033 at $V_{GS} = 3.0$ V	4.2	
	0.035 at $V_{GS} = 2.5$ V	3.9	

FEATURES

- Halogen-free
- Low $R_{DS(on)}$
- V_{GS} Max Rating: 14 V
- Exceeds 2 kV ESD Protection


RoHS
COMPLIANT

DESCRIPTION

The Si6926AEDQ is a dual N-Channel MOSFET with ESD protection and gate over-voltage protection circuitry incorporated into the MOSFET. The device is designed for use in Lithium Ion battery pack circuits. The 2-stage input protection circuit is a unique design, consisting of two stages of back-to-back zener diodes separated by a resistor. The first stage diode is designed to absorb most of the ESD energy. The second stage diode is designed to protect the gate from any remaining ESD energy and over-voltages

above the gates inherent safe operating range. The series resistor used to limit the current through the second stage diode during over voltage conditions has a maximum value which limits the input current to ≤ 10 mA at 14 V and the maximum t_{off} to 15 μ s. The Si6926AEDQ has been optimized as a battery or load switch in Lithium Ion applications with the advantage of both a 2.5 V $R_{DS(on)}$ rating and a safe 14 V gate-to-source maximum rating.

APPLICATION CIRCUITS

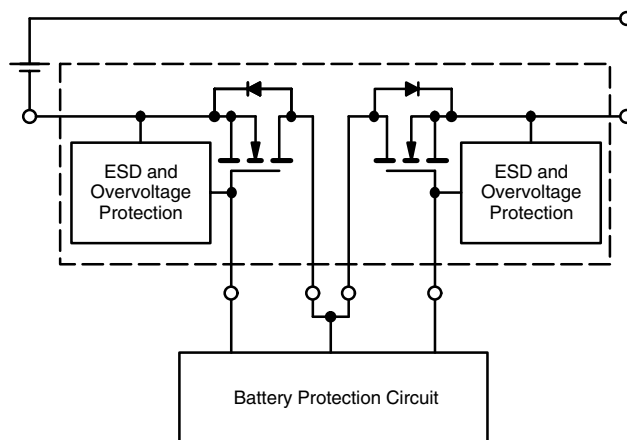
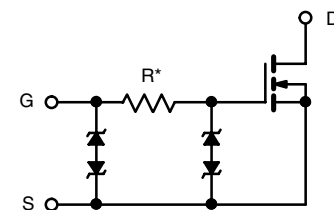


Figure 1. Typical Use In a Lithium Ion Battery Pack

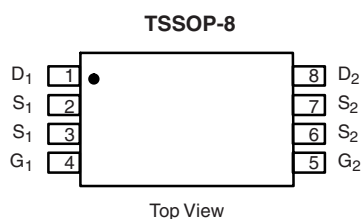


*R typical value is 1.9 k Ω by design.

See Typical Characteristics,
Gate-Current vs. Gate-Source Voltage, Page 3.

Figure 2. Input ESD and Overvoltage Protection Circuit

FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION



Ordering Information: Si6926AEDQ-T1-GE3 (Lead (Pb)-free and Halogen-free)

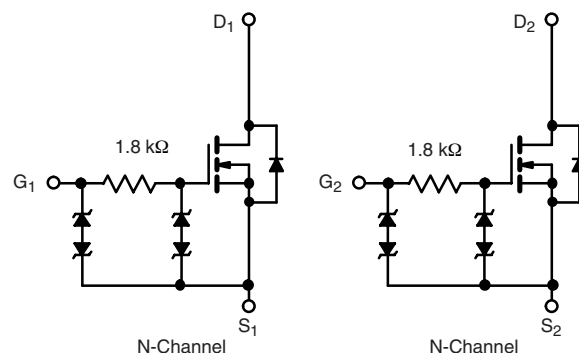


Figure 3.

Figure 4.

ABSOLUTE MAXIMUM RATINGS $T_A = 25\text{ }^{\circ}\text{C}$, unless otherwise noted				
Parameter	Symbol	10 s	Steady State	Unit
Drain-Source Voltage, Source-Drain Voltage	V_{DS}	20		V
Gate-Source Voltage	V_{GS}	± 14		
Continuous Drain-to-Source Current ($T_J = 150\text{ }^{\circ}\text{C}$) ^a	I_D	4.5	4.1	A
		3.6	3.3	
Pulsed Drain-to-Source Current	I_{DM}	20		A
Pulsed Source Current (Diode Conduction) ^a	I_S	0.83	0.69	
Maximum Power Dissipation ^a	P_D	1.0	0.83	W
		0.64	0.53	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	- 55 to 150		$^{\circ}\text{C}$

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10\text{ s}$	R_{thJA}	90	125	$^{\circ}\text{C/W}$
	Steady State		126	150	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	65	80	

Notes:

a. Surface Mounted on FR4 board.

SPECIFICATIONS $T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = 250\text{ }\mu\text{A}$	0.4		1.2	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 4.5\text{ V}$			± 1	μA
		$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 12\text{ V}$			± 10	mA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 20\text{ V}$, $V_{GS} = 0\text{ V}$			1	μA
		$V_{DS} = 20\text{ V}$, $V_{GS} = 0\text{ V}$, $T_J = 55\text{ }^{\circ}\text{C}$			5	
On-State Drain Current ^b	$I_{D(on)}$	$V_{DS} \geq 5\text{ V}$, $V_{GS} = 5\text{ V}$	10			A
Drain-Source On-State Resistance ^b	$R_{DS(on)}$	$V_{GS} = 4.5\text{ V}$, $I_D = 4.5\text{ A}$		0.023	0.030	Ω
		$V_{GS} = 3.0\text{ V}$, $I_D = 4.2\text{ A}$		0.025	0.033	
		$V_{GS} = 2.5\text{ V}$, $I_D = 3.9\text{ A}$		0.027	0.035	
Forward Transconductance ^b	g_{fs}	$V_{DS} = 10\text{ V}$, $I_D = 4.5\text{ A}$		26		S
Diode Forward Voltage ^b	V_{SD}	$I_S = 0.83\text{ A}$, $V_{GS} = 0\text{ V}$		0.65	1.1	V
Dynamic^a						
Total Gate Charge	Q_g	$V_{DS} = 10\text{ V}$, $V_{GS} = 4.5\text{ V}$, $I_D = 4.5\text{ A}$		7.6	12	nC
Gate-Source Charge	Q_{gs}			1.5		
Gate-Drain Charge	Q_{gd}			1.5		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 10\text{ V}$, $R_L = 10\text{ }\Omega$ $I_D \approx 1\text{ A}$, $V_{GEN} = 4.5\text{ V}$, $R_g = 6\text{ }\Omega$		0.43	0.7	μs
Rise Time	t_r			0.8	1.2	
Turn-Off Delay Time	$t_{d(off)}$			5.0	7.5	
Fall Time	t_f			2.5	4.0	

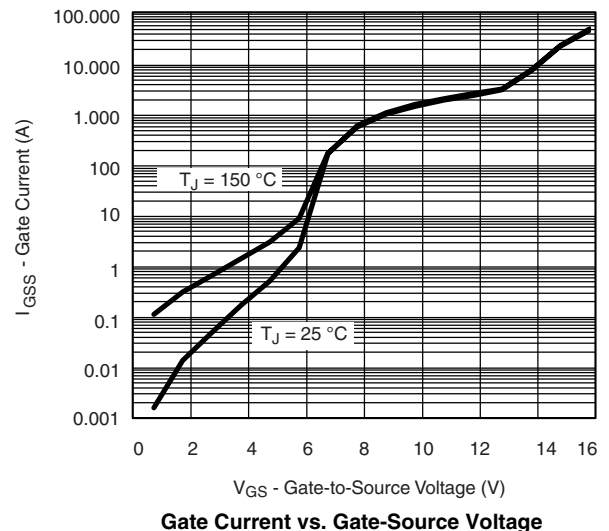
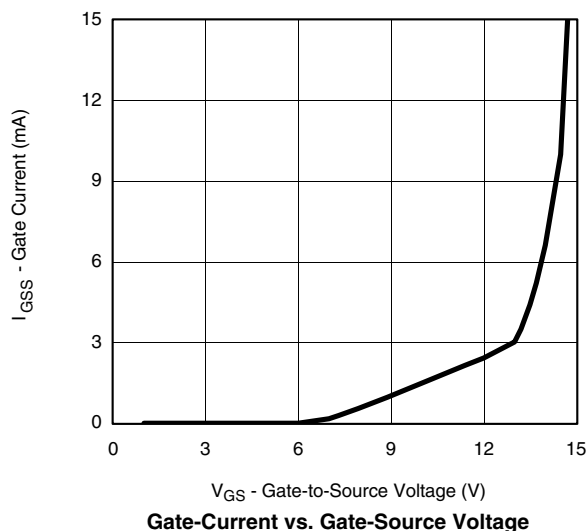
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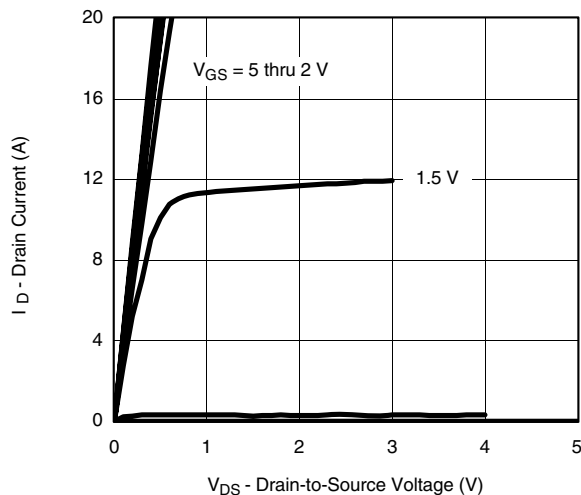
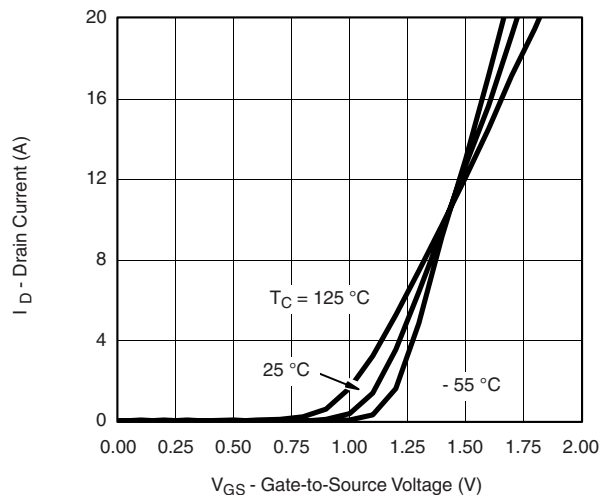
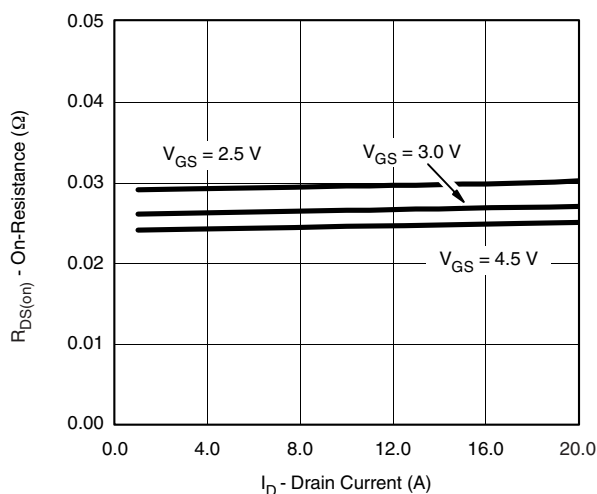
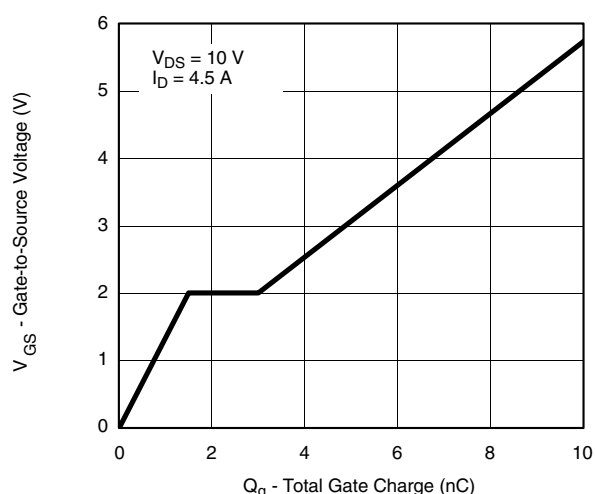
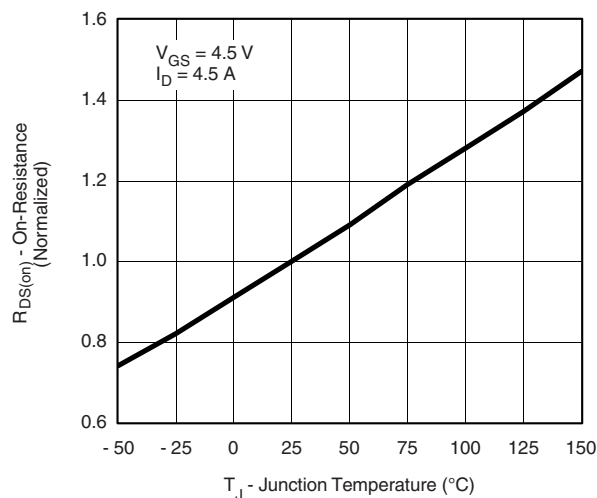
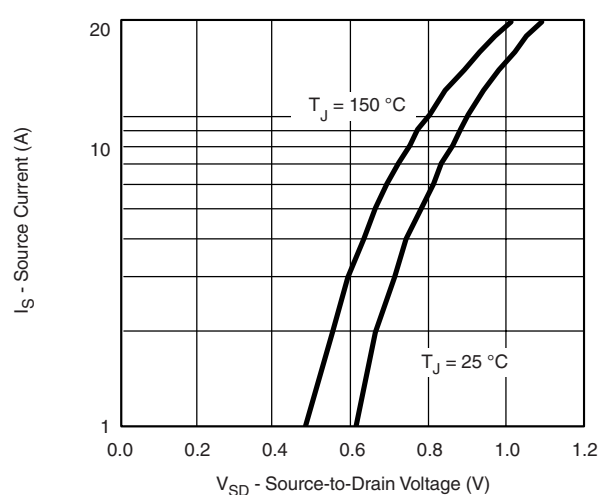
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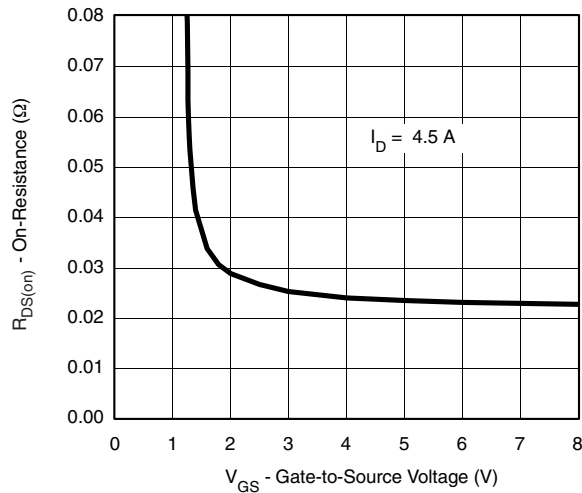
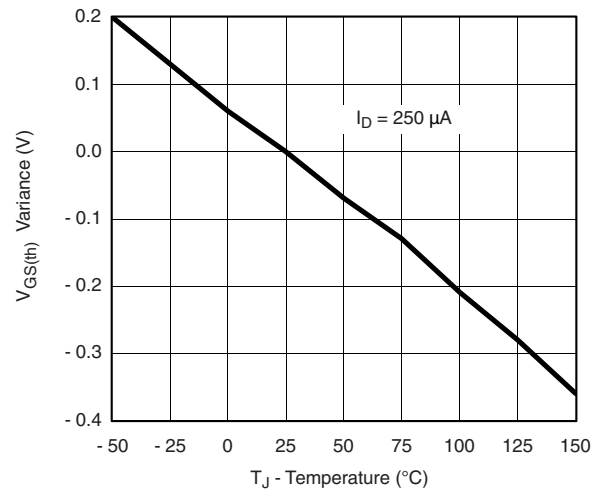
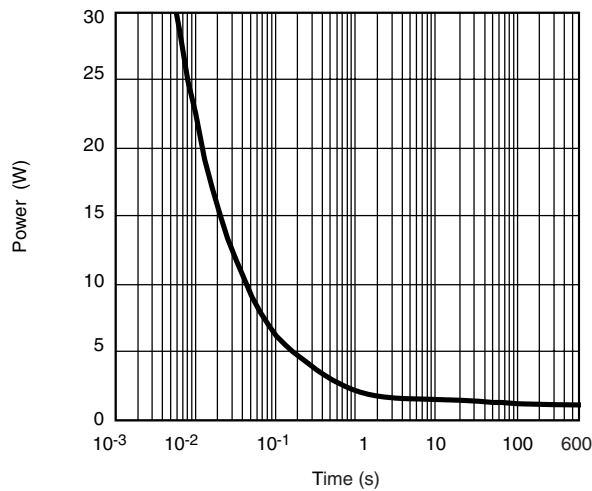
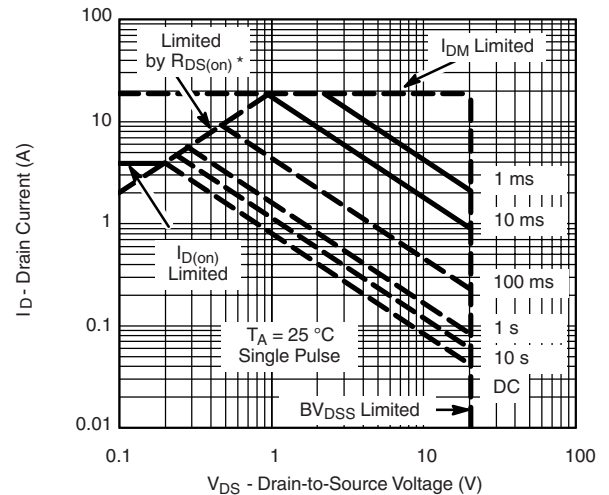
b. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

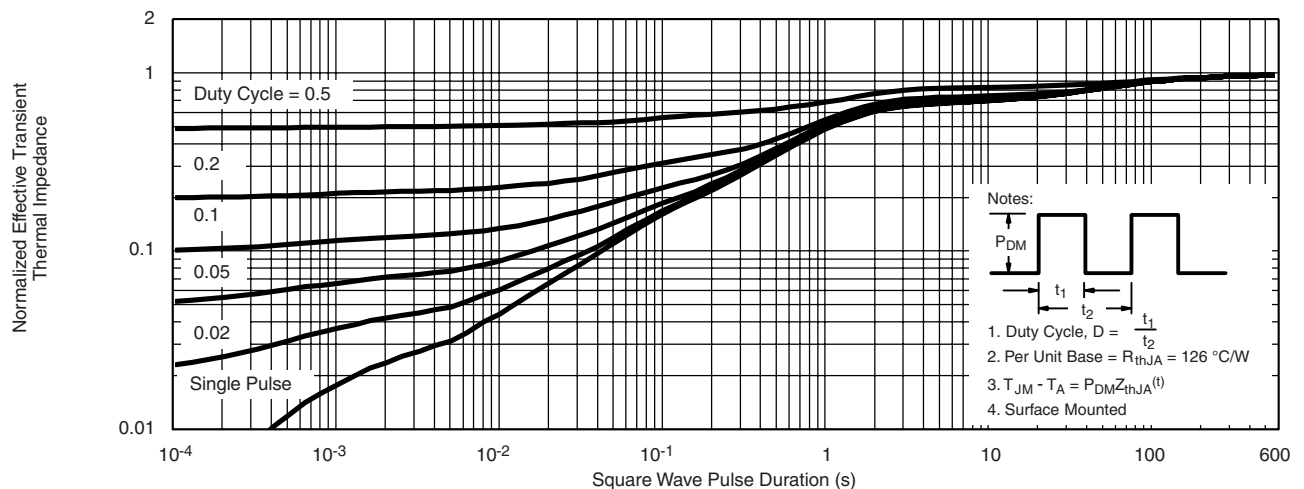
TYPICAL CHARACTERISTICS $25\text{ }^{\circ}\text{C}$, unless otherwise noted



TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted**Output Characteristics****Transfer Characteristics****On-Resistance vs. Drain Current****Gate Charge****On-Resistance vs. Junction Temperature****Source-Drain Diode Forward Voltage**

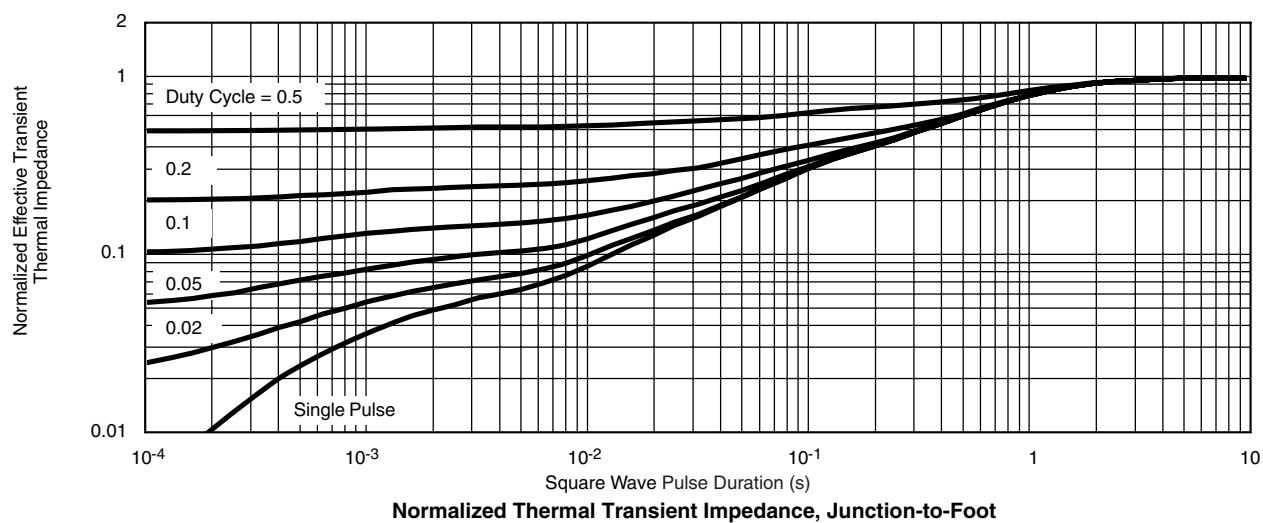
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Single Pulse Power, Junction-to-Ambient


* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Case


Notes:

1. Duty Cycle, $D = \frac{t_1}{t_2}$
2. Per Unit Base = $R_{thJA} = 126$ °C/W
3. $T_{JM} - T_A = P_{DM} Z_{thJA}(t)$
4. Surface Mounted

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

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